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## FGD3N60UNDF 600 V, 3 A **Short Circuit Rated IGBT**

#### **Features**

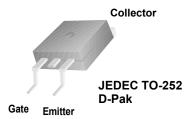
- Short Circuit Rated 10us
- · High Current Capability
- · High Input Impedance
- · Fast Switching
- · RoHS Compliant

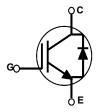
#### **Applications**

· Sewing Machine, CNC, Home Appliances, Motor Control

#### **General Description**

Using advanced NPT IGBT technology, Fairchild®'s the NPT IGBTs offer the optimum performance for low-power inverterdriven applications where low-losses and short-circuit ruggedness features are essential.





### **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 20	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	6	Α
	Collector Current	@ T <sub>C</sub> = 100°C	3	Α
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	9	Α
l <sub>F</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	3	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	60	W
' D	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	24	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case		2.08	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case		5.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)		150	°C/W

2: Mounted on 1" square PCB (FR4 or G-10 material)

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

## **Package Marking and Ordering Information**

Device Marking Device		Package	Rel Size	Tape Width	Quantity
FGD3N60UNDF	FGD3N60UNDF	TO252	330mm	16mm	2500 units

## Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250\mu A$	600	-	-	V
$\Delta BV_{DSS} \over \Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	-	0.3	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±10	uA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C$ = 3mA, $V_{CE}$ = $V_{GE}$	5.5	6.8	8.5	V
		I <sub>C</sub> = 3A, V <sub>GE</sub> = 15V	-	2.0	2.52	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 3A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C	-	2.4	-	V
Dynamic C	haracteristics					
C <sub>ies</sub>	Input Capacitance		-	165		pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$	-	28		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz	-	8.5		pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	5.5		ns
t <sub>r</sub>	Rise Time		-	1.8		ns
$t_{d(off)}$	Turn-Off Delay Time	V <sub>CC</sub> = 400V, I <sub>C</sub> = 3A,	-	22		ns
t <sub>f</sub>	Fall Time	$R_{G} = 10\Omega, V_{GE} = 15V,$	-	91		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	52		uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	30		uJ
E <sub>ts</sub>	Total Switching Loss		-	82		uJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	4.8		ns
t <sub>r</sub>	Rise Time		-	2.6		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V = 400V I- = 3A	-	24		ns
t <sub>f</sub>	Fall Time	$V_{CC}$ = 400V, $I_C$ = 3A, $R_G$ = 10 $\Omega$ , $V_{GE}$ = 15V, Inductive Load, $T_C$ = 125°C	-	122		ns
E <sub>on</sub>	Turn-On Switching Loss		-	65		uJ
E <sub>off</sub>	Turn-Off Switching Loss			44		uJ
E <sub>ts</sub>	Total Switching Loss		_	109		uJ
T <sub>sc</sub>	Short Circuit Withstand Time	$V_{CC} = 350V,$ $R_G = 100\Omega, V_{GE} = 15V,$ $T_C = 150^{\circ}C$	10			us

## Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Qg	Total Gate Charge		-	1.6	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CE</sub> = 400V, I <sub>C</sub> = 3A, V <sub>GE</sub> = 15V	-	6.6	-	nC
$Q_{gc}$	Gate to Collector Charge		-	11.3	-	nC

## Electrical Characteristics of the Diode T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V <sub>FM</sub>	Diode Forward Voltage	I <sub>E</sub> = 3A	T <sub>C</sub> = 25°C	-	1.7	2.2	V
V <sub>FM</sub> Blode i si wara voltage	1F 07 (	T <sub>C</sub> = 125°C	-	1.6	-		
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> =3A, dI <sub>F</sub> /dt = 200A/μs	T <sub>C</sub> = 25°C	-	21	-	ns
भा			T <sub>C</sub> = 125°C	-	31	-	110
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>C</sub> = 25°C	-	23	-	nC
α <sub>II</sub>			T <sub>C</sub> = 125°C	-	49	-	

Figure 1. Typical Output Characteristics

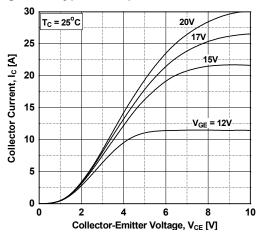


Figure 3. Typical Saturation Voltage Characteristics

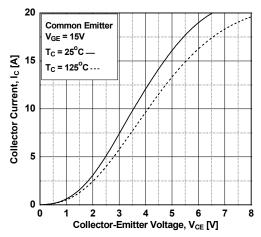


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

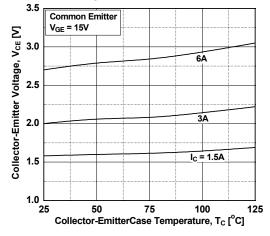


Figure 2. Typical Output Characteristics

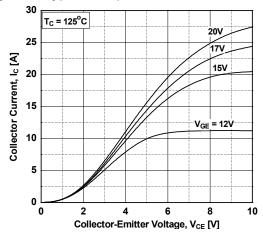


Figure 4. Transfer Characteristics

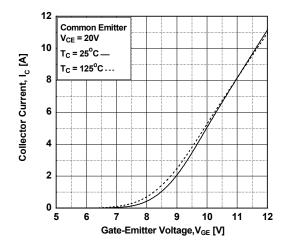


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

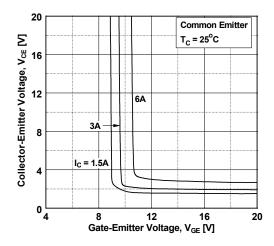


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

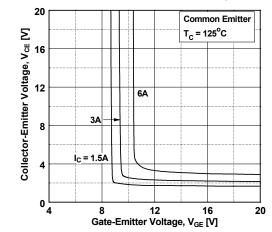


Figure 9. Gate charge Characteristics

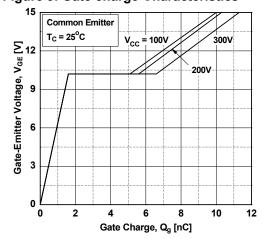


Figure 11. Turn-on Characteristics vs.
Gate Resistance

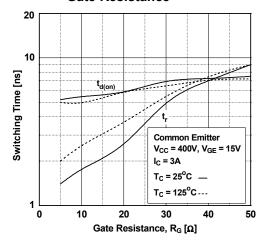


Figure 8. Capacitance Characteristics

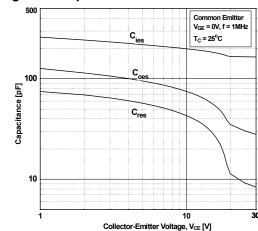


Figure 10. SOA Characteristics

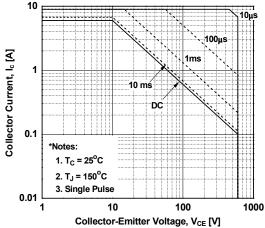


Figure 12. Turn-off Characteristics vs.
Gate Resistance

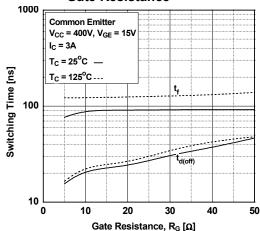


Figure 13. Turn-on Characteristics vs.
Collector Current

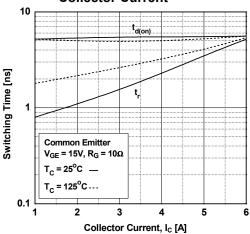


Figure 15. Switching Loss vs.
Gate Resistance

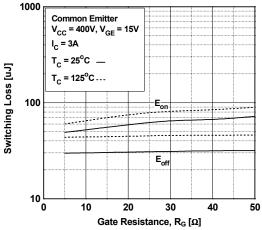


Figure 17. Turn off Switching SOA Characteristics

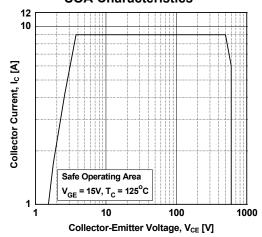


Figure 14. Turn-off Characteristics vs. Collector Current

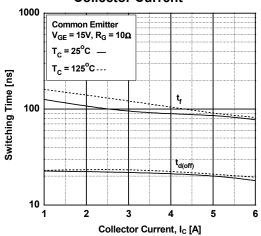


Figure 16. Switching Loss vs Collector Current

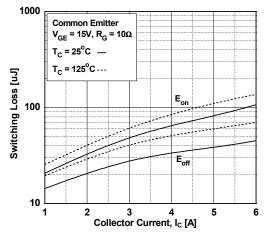
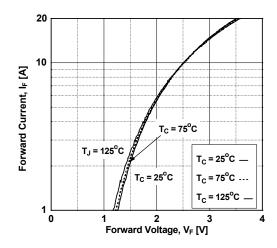


Figure 18. Forward Characteristics



#### Figure 19. Reverse Recovery Current

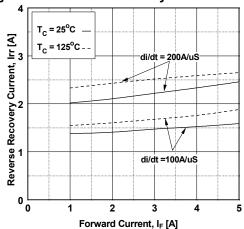


Figure 20. Stored Charge

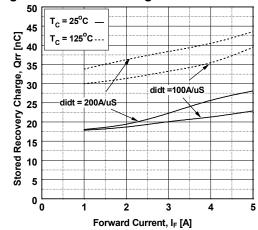


Figure 21. Reverse Recovery Time

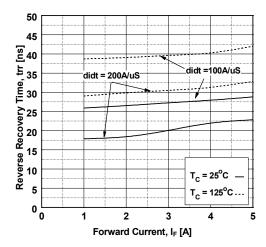


Figure 22. Transient Thermal Impedance of IGBT

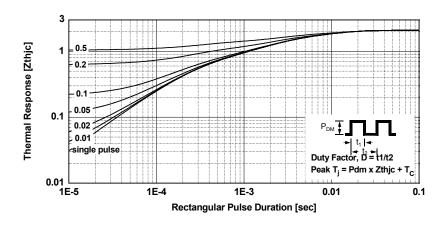
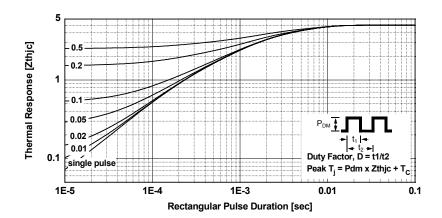
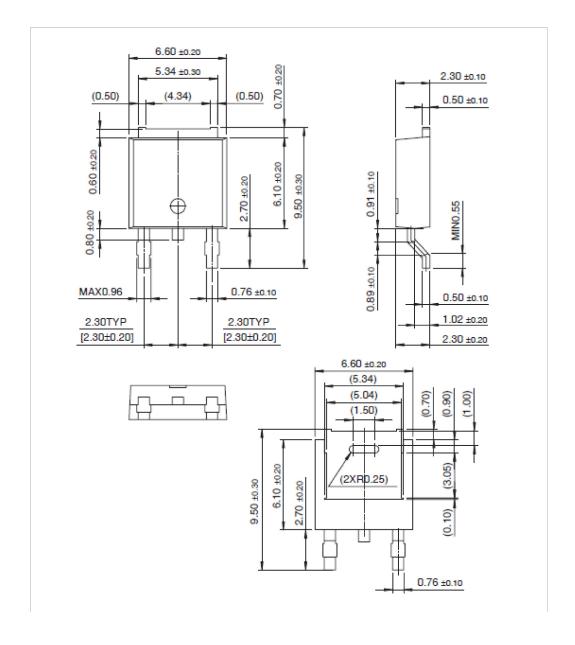


Figure 23. Transient Thermal Impedance of FRD



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## **D-PAK**







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 IKFW50N65EH5XKSA1
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 IDW40E65D2FKSA1